



PATENTS
MIC-24 Cont.

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

PATENT APPLICATION

Applicants : Kie Y. Ahn et al.
Application No. : 10/644,278 Confirmation No. : 5174
Filed : August 19, 2003
For : SEMICONDUCTOR DEVICE WITH
ELECTRICALLY COUPLED SPIRAL INDUCTORS
Group Art Unit : 1765

New York, New York 10020
September 29, 2003

Hon. Commissioner for Patents
P.O. Box 1450
Alexandria, Virginia 22313-1450

INFORMATION DISCLOSURE STATEMENT

Sir:

Pursuant to 37 C.F.R. §§ 1.56 and 1.97, applicants hereby make the following patents and publications of record in the above-identified patent application:

Farrar et al. U.S. Patent 6,025,261 (February 15, 2000)
Wen et al. U.S. Patent 6,083,802 (July 4, 2000)
Forbes U.S. Patent 6,107,893 (August 22, 2000)
Forbes et al. U.S. Patent 6,191,468 (February 20, 2001)
Forbes U.S. Patent 6,201,287 (March 13, 2001)
Farrar et al. U.S. Patent 6,239,684 (May 29, 2001)
Ahn et al. U.S. Patent 6,240,622 (June 5, 2001)
Noble et al. U.S. Patent 6,245,615 (June 12, 2001)
Forbes U.S. Patent 6,249,191 (June 19, 2001)
Forbes et al. U.S. Patent 6,251,470 (June 26, 2001)
Ahn et al. U.S. Patent 6,277,728 (August 21, 2001)
Forbes et al. U.S. Patent 6,287,932 (September 11, 2001)
Forbes U.S. Patent 6,414,550 (July 2, 2002)
Ahn et al. U.S. Patent 6,420,954 (July 16, 2002)
Acosta et al. U.S. Patent 6,492,708 (December 10, 2002)
Ahn et al. U.S. Patent 6,535,101 (March 18, 2003)

Xu et al. U.S. Patent Application Publication
2003/0071325 (April 17, 2003)

Bassous, E., "Fabrication of Novel
Three-Dimensional Microstructures by the Anisotropic
Etching of (100) and (110) Silicon," IEEE Transactions
on Electron Devices, vol. ED-25, no. 10, pp. 1178-85
(October 1978)

Brodie, I., et al., The Physics of
Microfabrication, pp. 1-78 (Plenum Press, New York 1982)

Burghartz, J., et al., "Integrated RF and Microwave
Components in BiCMOS Technology," IEEE Transactions on
Electron Devices, vol. 43, no. 9, pp. 1559-70
(September 1996)

Burghartz, J., et al., "Multilevel-Spiral Inductors
Using VLSI Interconnect Technology," IEEE Electron
Device Letters, vol. 17, no. 9, pp. 428-30
(September 1996)

Chang, J.Y.-C., et al., "Large Suspended Inductors
on Silicon and Their Use in a 2-*m CMOS RF Amplifier,"
IEEE Electron Device Letters, vol. 14, no. 5, pp. 246-48
(May 1993)

Frye, R.C., et al., "Inductive Crosstalk Between
Integrated Passive Components in RF-Wireless Modules,"
IEEE Proceedings of the 1998 International Conference on
Multichip Modules and High Density Packaging, pp. 496-
500 (1998)


Pieters, P., et al., "Spiral Inductors Integrated
in MCM-D using the Design Space Concept," IEEE
Proceedings of the 1998 International Conference on
Multichip Modules and High Density Packaging, pp. 478-83
(1998)

Each of the aforementioned patents and publications, which
are listed on the accompanying Form PTO-1449 (submitted in
duplicate), were cited by applicants or the Examiner in
parent Application No. 10/008,900, with the exception of
Patents Nos. 6,414,550, 6,420,954 and 6,535,101 (which were
cited as unpublished applications). Accordingly, pursuant to
37 C.F.R. § 1.98(d), no copies are enclosed, except of
Patents Nos. 6,414,550, 6,420,954 and 6,535,101.

It is respectfully requested that these patents and publications be (1) fully considered by the Patent and Trademark Office during examination of this application; and (2) printed on any patent which may issue on this application. Applicants request that a copy of Form PTO-1449, as considered and initialled by the Examiner, be returned with the next communication.

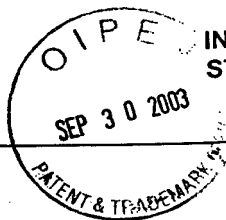
An early and favorable action is respectfully requested.

Respectfully submitted,



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FORM PTO-1449

U.S. DEPARTMENT OF COMMERCE
PATENT AND TRADEMARK OFFICEATTY. DOCKET NO.
MIC-24 Cont.APPLN. NO.
10/644,278APPLICANT
Kie Y. Ahn et al.CONF. NO.
5174FILING DATE
August 19, 2003GROUP ART UNIT
1765INFORMATION DISCLOSURE
STATEMENT BY APPLICANT

U.S. PATENT DOCUMENTS

EXAMINER INITIAL	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
	6,025,261	2/2000	Farrar et al.	438	619	
	6,083,802	7/2000	Wen et al.	438	381	
	6,107,893	8/2000	Forbes	331	132	
	6,191,468	2/2001	Forbes et al.	257	531	
	6,201,287	3/2001	Forbes	257	528	
	6,239,684	5/2001	Farrar et al.	336	200	
	6,240,622	6/2001	Ahn et al.	29	604	
	6,245,615	6/2001	Noble et al.	438	270	
	6,249,191	6/2001	Forbes	331	117FE	
	6,251,470	6/2001	Forbes et al.	427	97	
	6,277,728	8/2001	Ahn et al.	438	619	
	6,287,932	9/2001	Forbes et al.	438	381	
	6,414,550	7/2002	Forbes	330	264	
	6,420,954	7/2002	Ahn et al.	336	232	
	6,492,708	12/2002	Acosta et al.	257	531	
	6,535,101	3/2003	Ahn et al.	336	232	
	2003/0071325	4/2003	Xu et al.	257	531	

FOREIGN PATENT DOCUMENTS

EXAMINER INITIAL	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION	
						YES	NO

EXAMINER

DATE CONSIDERED

EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

FORM PTO-1449

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OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)

EXAMINER INITIAL	
	Bassous, E., "Fabrication of Novel Three-Dimensional Microstructures by the Anisotropic Etching of (100) and (110) Silicon," <u>IEEE Transactions on Electron Devices</u> , vol. ED-25, no. 10, pp. 1178-85 (October 1978)
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